

Marcelo Nelson PÃ¡ez CarreÃ±o

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8197859/publications.pdf>

Version: 2024-02-01

50
papers

653
citations

567281

15
h-index

610901

24
g-index

50
all docs

50
docs citations

50
times ranked

481
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultrasensitive microfluidic electrochemical immunosensor based on electrodeposited nanoporous gold for SOX-2 determination. <i>Analytica Chimica Acta</i> , 2020, 1127, 122-130.	5.4	21
2	Development of MEMS based microCVD technique for new materials thin films deposition. , 2019, , .		0
3	Multiphase Thermal-fluid Flow through Geothermal Reservoirs. <i>Energy Procedia</i> , 2016, 95, 22-28.	1.8	3
4	Challenges to implementing a ballast water remote monitoring system. <i>Ocean and Coastal Management</i> , 2016, 131, 25-38.	4.4	6
5	Miniature Planar Fluxgate Magnetic Sensors Using a Single Layer of Coils. <i>IEEE Sensors Journal</i> , 2015, 15, 2365-2369.	4.7	11
6	Microfluidic biochip for phytoplankton cell counting. , 2013, , .		1
7	Simulation of PECVD SiO ₂ Deposition Using a Cellular Automata Approach. <i>ECS Transactions</i> , 2012, 49, 297-304.	0.5	3
8	Simulator for Microfluidics Based on the Lattice Boltzmann Method. <i>ECS Transactions</i> , 2011, 39, 461-468.	0.5	3
9	A Multi-Process Microfabrication Simulator on Cellular Automata. <i>ECS Transactions</i> , 2010, 31, 101-108.	0.5	1
10	Microfluidic Systems in PDMS for Study of Foraging Abilities of Marine Microorganisms. <i>ECS Transactions</i> , 2010, 31, 449-455.	0.5	0
11	Integration of optical waveguides with micro-incandescent light. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 2538-2543.	3.1	5
12	PECVD a-Si:H Young's modulus obtained by MEMS resonant frequency. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 2359-2364.	3.1	8
13	Complete Microfluidic System Fabricated in Glass Substrates. <i>ECS Transactions</i> , 2008, 14, 47-56.	0.5	3
14	Piezoelectric Stimulation of Microcantilever Beams for Young's Modulus Determination of Amorphous Hydrogenated Silicon Carbide. <i>ECS Transactions</i> , 2008, 14, 63-71.	0.5	3
15	3D Simulation Software for Visualization of MEMS Microfabrication Processes. <i>ECS Transactions</i> , 2008, 14, 99-108.	0.5	0
16	Simulation of Anisotropic Etching of Silicon using a Cellular Automata Model. <i>ECS Transactions</i> , 2008, 14, 37-46.	0.5	0
17	Silicon Microtips with Self-Asigned Integrated Electrodes. <i>ECS Transactions</i> , 2007, 9, 473-480.	0.5	0
18	Simple MEMS-based Incandescent Microlamps. <i>ECS Transactions</i> , 2007, 9, 489-496.	0.5	1

#	ARTICLE	IF	CITATIONS
19	Thermally actuated a-SiC:H MEMS fabricated by a PECVD process. Journal of Non-Crystalline Solids, 2006, 352, 1822-1828.	3.1	12
20	Post thermal annealing crystallization and reactive ion etching of SiC films produced by PECVD. Journal of Non-Crystalline Solids, 2006, 352, 1392-1397.	3.1	31
21	Amorphous and excimer laser annealed SiC films for TFT fabrication. Solid-State Electronics, 2006, 50, 241-247.	1.4	12
22	N and p-type doping of PECVD a-SiC:H obtained under æsilane starving plasmaæ condition with and without hydrogen dilution. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 128, 44-49.	3.5	15
23	Modification of electrode materials for plasma torches. Surface and Coatings Technology, 2005, 200, 254-257.	4.8	3
24	Fabrication of PECVD-silicon oxynitride-based optical waveguides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 112, 154-159.	3.5	18
25	Structural and electrical properties of low-temperature PECVD SiC/c-Si heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 112, 144-146.	3.5	7
26	Hydrogen effusion from highly-ordered near-stoichiometric a-SiC:H. Journal of Non-Crystalline Solids, 2004, 338-340, 70-75.	3.1	4
27	Self-sustained bridges of a-SiC:H films obtained by PECVD at low temperatures for MEMS applications. Journal of Non-Crystalline Solids, 2004, 338-340, 490-495.	3.1	21
28	Membranes of SiOxNy with 3D topography formed by PECVD for MEMS applications. Journal of Non-Crystalline Solids, 2004, 338-340, 788-792.	3.1	12
29	Preparation and characterization of nanocrystalline h-BN films prepared by PECVD method. Brazilian Journal of Physics, 2002, 32, 372-375.	1.4	7
30	PECVD-SiOxNy films for large area self-sustained grids applications. Sensors and Actuators A: Physical, 2002, 100, 295-300.	4.1	26
31	Mechanical and thermophysical properties of PECVD oxynitride films measured by MEMS. Thin Solid Films, 2001, 398-399, 626-631.	1.8	5
32	Optimization of the i-layer width of Cr-a-Si:H PIN X-ray detectors. Thin Solid Films, 2001, 396, 237-241.	1.8	1
33	Wide optical band gap window layers for solar cells. Solar Energy Materials and Solar Cells, 2001, 66, 155-162.	6.2	46
34	Sample preparation method for scanning force microscopy. Brazilian Journal of Physics, 2001, 31, .	1.4	2
35	Mechanical properties of boron nitride thin films obtained by RF-PECVD at low temperatures. Thin Solid Films, 2000, 373, 273-276.	1.8	23
36	Highly ordered amorphous silicon-carbon alloys obtained by RF PECVD. Brazilian Journal of Physics, 2000, 30, 533-540.	1.4	4

#	ARTICLE	IF	CITATIONS
37	p-Type doping in a-Si _{1-x} C _x :H obtained by PECVD. Journal of Non-Crystalline Solids, 2000, 266-269, 699-703.	3.1	7
38	Observation of Negative Differential Resistance in $\mu\text{-Si:H/a-Si}_{1-x}\text{C}_x\text{:H}$ Double Barrier Devices. Japanese Journal of Applied Physics, 1999, 38, 1317-1319.	1.5	1
39	Thick SiO _x N _y and SiO ₂ films obtained by PECVD technique at low temperatures. Thin Solid Films, 1998, 332, 40-45.	1.8	58
40	N-type doping in PECVD a-Si _{1-x} C _x :H obtained under 'starving plasma' condition. Journal of Non-Crystalline Solids, 1998, 227-230, 483-487.	3.1	11
41	The influence of 'starving plasma' regime on carbon content and bonds in a-Si _{1-x} C _x :H thin films. Journal of Applied Physics, 1998, 84, 2371-2379.	2.5	44
42	Low temperature plasma enhanced chemical vapour deposition boron nitride. Thin Solid Films, 1997, 308-309, 219-222.	1.8	35
43	Wide gap a-Si _{1-x} C _x :H thin films obtained under starving plasma deposition conditions. Journal of Non-Crystalline Solids, 1996, 201, 110-118.	3.1	30
44	On the structural properties of a-Si _{1-x} C _x :H thin films. Journal of Applied Physics, 1996, 79, 1324-1329.	2.5	36
45	Effect of plasma etching, carbon concentration, and buffer layer on the properties of a-Si:H/a-Si _{1-x} C _x :H multilayers. Journal of Applied Physics, 1994, 75, 543-548.	2.5	6
46	Microvoids in diamond-like amorphous silicon carbide. Journal of Applied Physics, 1994, 75, 538-542.	2.5	51
47	Negative conductance and sequential tunneling in amorphous silicon-silicon carbide double barrier devices. Journal of Non-Crystalline Solids, 1989, 110, 175-178.	3.1	10
48	Integral thin film technology amorphous silicon image sensor. Journal of Non-Crystalline Solids, 1989, 115, 90-92.	3.1	4
49	Negative resistance in a-SiC _x :H double barrier devices - frequency dependence. Journal of Non-Crystalline Solids, 1989, 114, 762-764.	3.1	11
50	Evidence of quantum size effects in a-Si:H/a-SiC _x :H superlattices. Observation of negative resistance in double barrier structures. Journal of Non-Crystalline Solids, 1987, 97-98, 871-874.	3.1	31